

Notice of References Cited	Application/Control No. 09/825,027	Applicant(s)/Patent Under Reexamination ROGERS ET AL.	
	Examiner Russell M Kobert	Art Unit 2829	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,404,222	06-2002	Fan et al.	324/765
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
	O					
	P					
	Q					
	R					
	S					
	T					

NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Chen et al (An On-Chip, Attifarad Interconnect Charge-Based Capacitance Measurement (CBCM) Technique, Chen, J.C.; McGaughy, B.W.; Sylvester, D.; Chenming Hu, Electron Devices Meeting, International, 8-11 Dec. 1996, Pages: 69 - 72)
	V	McGaughy et al (A Simple Method for On-Chip, Sub-Femto Farad Interconnect Capacitance Measurement, McGaughy, B.W.; Chen, J.C.; Sylvester, D.; Chenming Hu; Electron Device Letters, IEEE , Volume: 18, Issue: 1 , Jan. 1997, Pages: 21 - 23)
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.